

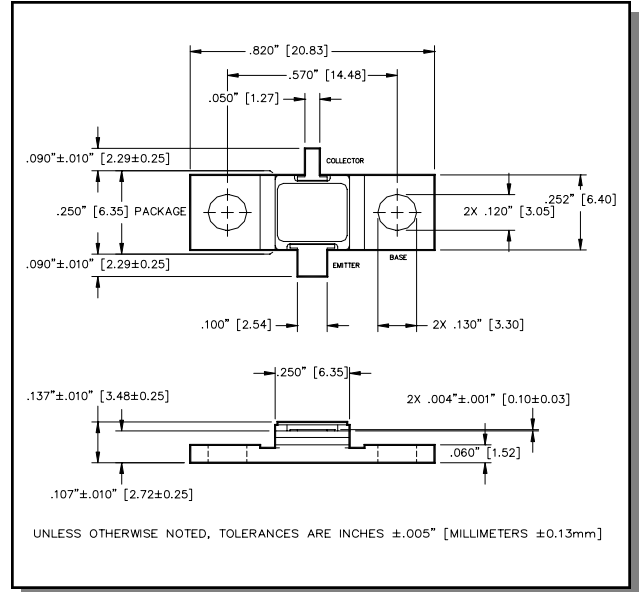
**Radar Pulsed Power Transistor**  
**2W, 1.2-1.4 GHz, 100µs Pulse, 10% Duty**

**M/A-COM Products**  
**Released, 30 May 07**

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	0.5	A
Power Dissipation @ +25°C	$P_{TOT}$	10.3	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

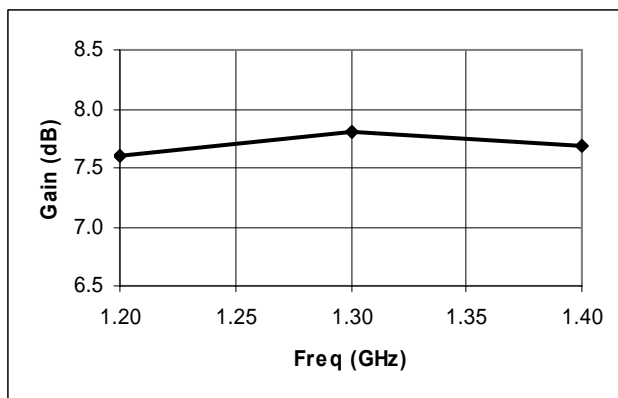
## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient )

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 4\text{mA}$		$BV_{CES}$	65	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		$I_{CES}$	-	0.50	mA
Thermal Resistance	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	17	°C/W
Output Power	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$P_{OUT}$	2.0	-	W
Power Gain	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$G_P$	7.0	-	dB
Collector Efficiency	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$\eta_C$	40	-	%
Input Return Loss	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-6	dB
Load Mismatch Tolerance	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 28\text{V}$ , $P_{in} = 0.40\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

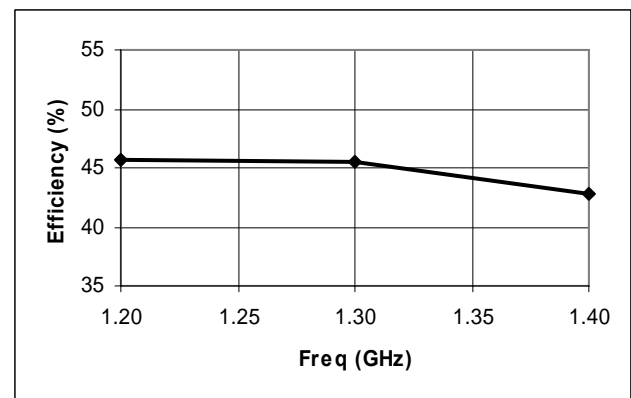
## Typical RF Performance

Freq. (GHz)	Pin (W)	Pin (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	0.40	2.3	7.60	0.18	45.7	-11.3	S	P
1.3	0.40	2.4	7.80	0.19	45.5	-13.6	S	P
1.4	0.40	2.4	7.69	0.20	42.8	-17.5	S	P

## Gain vs. Frequency

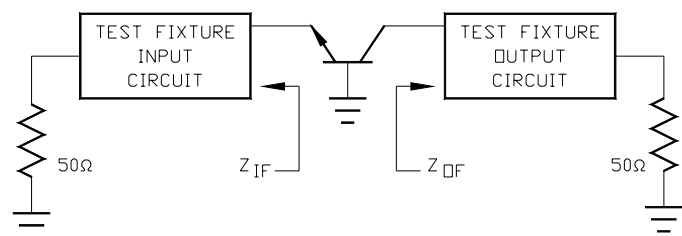


## Collector Efficiency vs. Frequency



## RF Test Fixture Impedance

F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
1.2	9.5 - j6.3	13.1 + j35.8
1.3	8.6 - j4.9	17.7 + j35.5
1.4	8.1 - j3.6	17.0 + j40.6



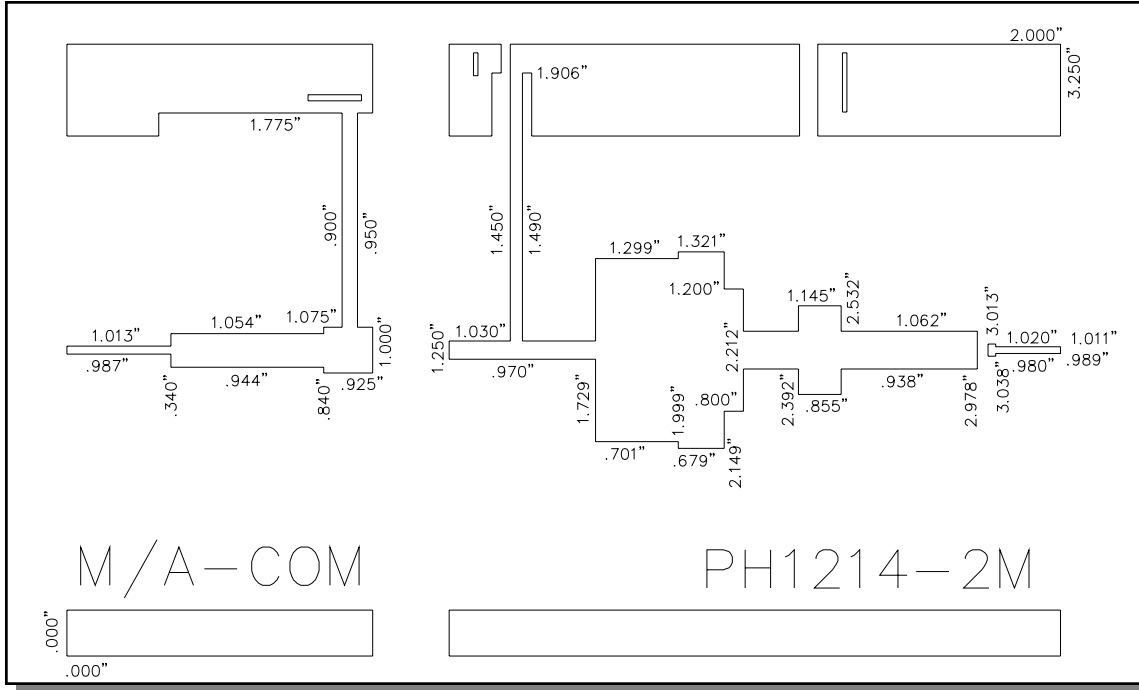
# PH1214-2M



Radar Pulsed Power Transistor  
2W, 1.2-1.4 GHz, 100µs Pulse, 10% Duty

M/A-COM Products  
Released, 30 May 07

## Test Fixture Circuit Dimensions



## Test Fixture Assembly

